

www.vishay.com

Vishay Semiconductors

Hyperfast Rectifier, 3 A FRED Pt®

eSMP® Series



Top View

Bottom View

SlimSMAW (DO-221AD)



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	3 A				
V_R	100 V, 200 V				
V _F at I _F	0.71 V				
I _{FSM}	70 A				
t _{rr} (typ.)	16 ns				
T _J max.	175 °C				
Package	SlimSMAW (DO-221AD)				
Circuit configuration	Single				

FEATURES

- Low profile package
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- COMPLIANT HALOGEN FREE

AUTOMOTIVE

- AEC-Q101 qualified, class 2 whisker test
- Compatible to SOD-128 package case outline
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial, and automotive applications.

MECHANICAL DATA

Case: SlimSMAW (DO-221AD)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage VS-3EYH01HM3	V		100	V		
VS-3EYH02HM3	- V _{RRM}		200	V		
Average rectified forward current	I _{F(AV)} (1)	T _C = 137 °C	3	А		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C, 10 ms sine pulse wave	70			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C		

Note

⁽¹⁾ Mounted on infinite heatsink

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	DL TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking	VS-3EYH01HM3	V_{BR}, V_{R}	I _R = 100 μA	100	-	-	V
voltage	VS-3EYH02HM3		Ι _R = 100 μΑ	200	-		
Forward voltage, per diode		V	I _F = 3 A	-	0.86	0.95	V
		V _F	I _F = 3 A, T _J = 150 °C	-	0.71	0.79	
Reverse leakage current, per diode		1	$V_R = V_R$ rated	-	-	2	
		I _R	T _J = 150 °C, V _R = V _R rated	-	-	20	μA
Junction capacitance		C _T	V _R = 200 V	-	16	-	pF



VS-3EYH01HM3, VS-3EYH02HM3

Vishay Semiconductors

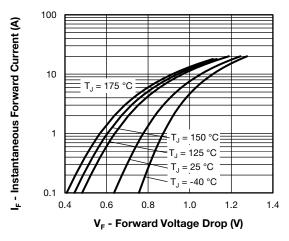
DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt =$	= 50 A/μs, V _R = 30 V	-	22	-	
		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	16	-	ns
	t _{rr}	I _F = 0.5 A, I _R = 1A, I _{rr} = 0.25 A		-	-	30	
		T _J = 25 °C	I _F = 3 A,	-	18	-	
		T _J = 125 °C		-	30	-	
Peak recovery current		T _J = 25 °C		-	2.5	-	^
	I _{RRM}	T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 100 \text{ V}$	-	4	-	Α
Reverse recovery charge		T _J = 25 °C		-	23	-	0
	Q _{rr}	T _J = 125 °C	1	-	60	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount		R _{thJM} ⁽¹⁾	Infinite heatsink	-	12	15	
Thermal resistance, junction to ambient		R _{thJA}	Device mounted on FR4 PCB, 2 oz. standard footprint	-	120	150	°C/W
Marking dayioo	VS-3EYH01HM3		Case style SlimSMAW (DO-221AD)	3H1			
Marking device	VS-3EYH02HM3		Case style SilitiSiviAW (DO-22 IAD)	3H2			

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

Vishay Semiconductors



100 I_R - Reverse Current (µA) 10 150 °C 1 125 °C 0.1 25 °C 0.01 0.001 0.0001 50 100 150 200 **V_R** - Reverse Voltage (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

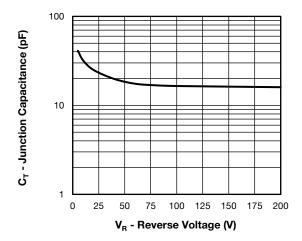


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

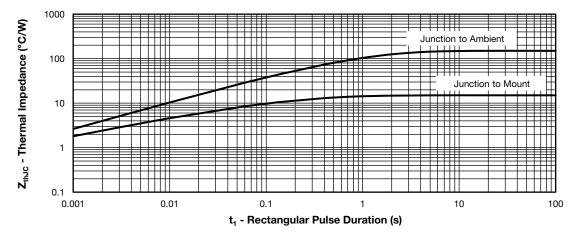


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

www.vishay.com

Vishay Semiconductors

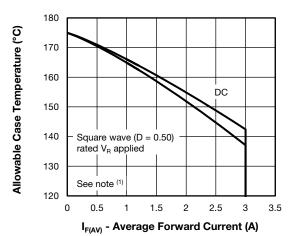
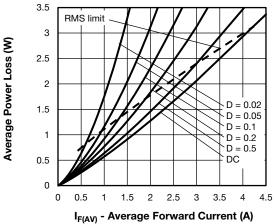
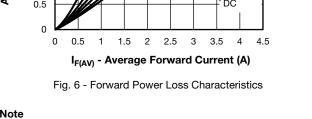


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current







⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

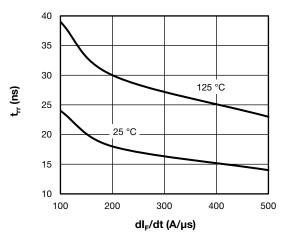


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

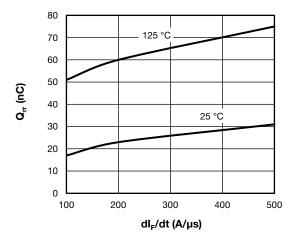


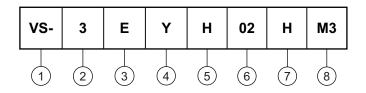
Fig. 8 - Typical Stored Charge vs. dl_F/dt

VS-3EYH01HM3, VS-3EYH02HM3

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (3 = 3 A)

Circuit configuration:

E = single diode

4 - Y = SlimSMAW (DO-221AD)

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-3EYH01HM3/H	0.033	Н	3500	7"diameter plastic tape and reel			
VS-3EYH01HM3/I	0.033	I	14 000	13"diameter plastic tape and reel			
VS-3EYH02HM3/H	0.033	Н	3500	7"diameter plastic tape and reel			
VS-3EYH02HM3/I	0.033	1	14 000	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96582</u>					
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96586				



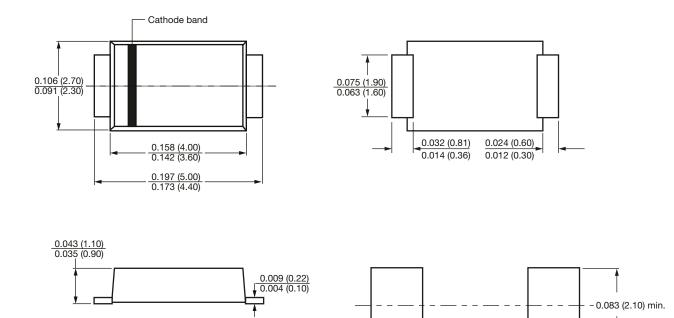
Vishay Semiconductors

0.055 (1.40) min.

SlimSMAW (DO-221AD)

DIMENSIONS in inches (millimeters)

SlimSMAW (DO-221AD)



0.055 (1.40) min.

Mounting pad layout

0.118 (3.00) max.

0.228 (5.80) ref.



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.